S1D010065G

TriQSiC™ 650V Silicon Carbide Schottky Diode G1

Features

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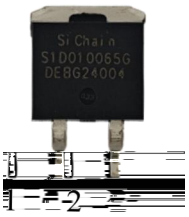

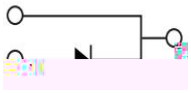

Benefits

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Applications

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Table 1 Key performance and package parameters

Type	V_{RRM}	I_F	Q_C	Marking	Package

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Features 1

Benefits 1

1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note

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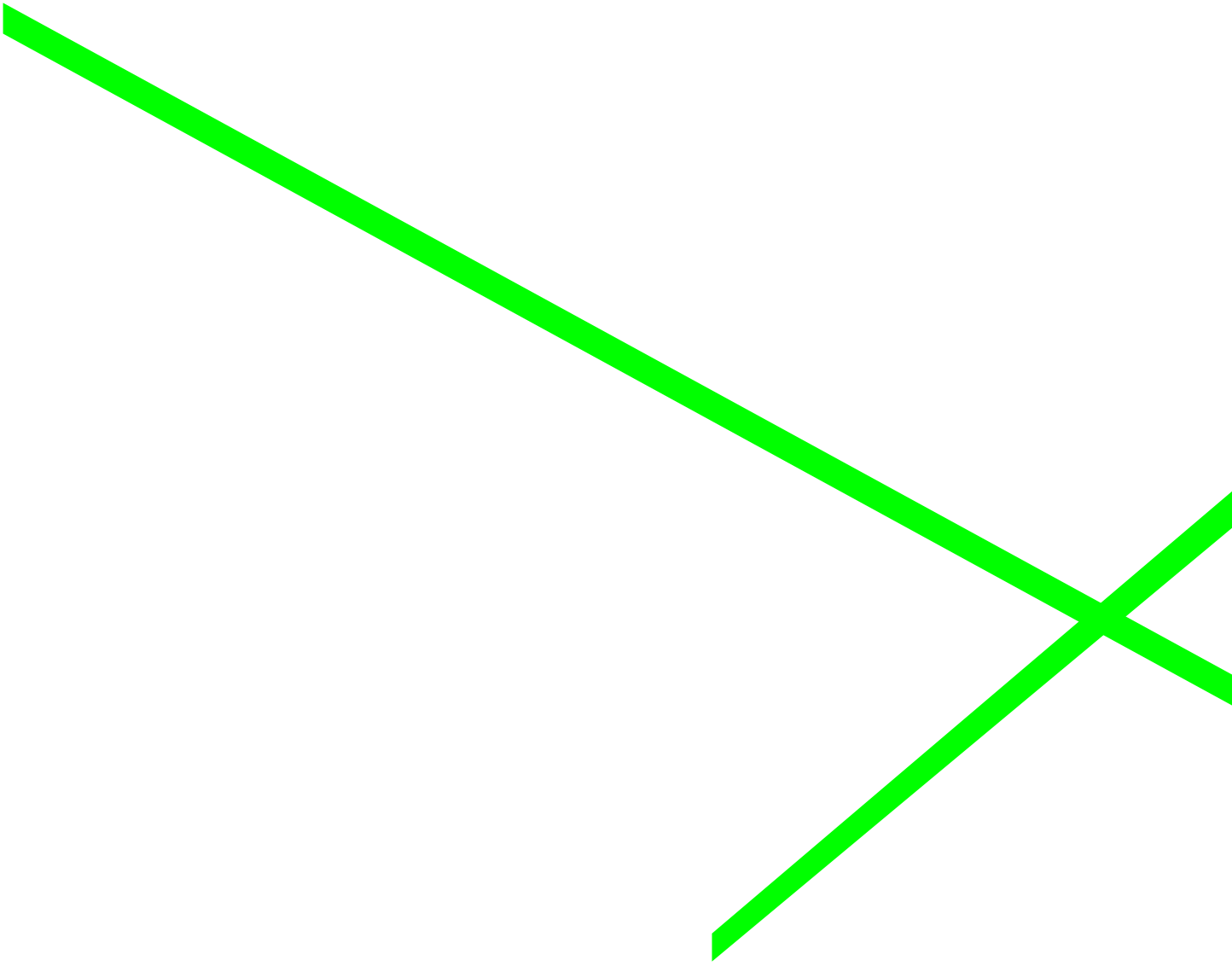

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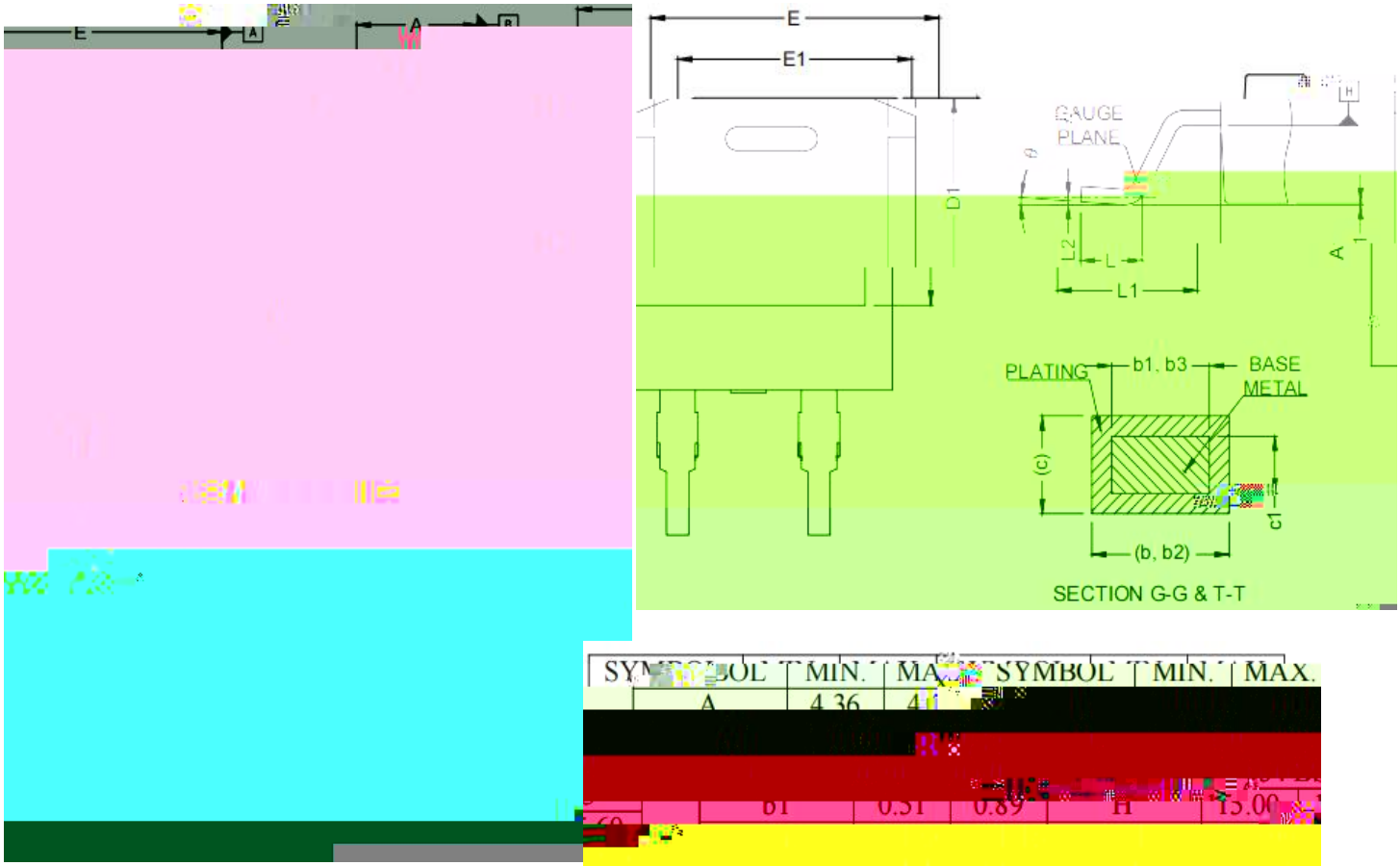
5 Package drawing



SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.
A	4.36	4.[illegible]			
b1	0.51	0.89	H	15.00	

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650V SiC Schottky Diode

Revision history

Document version	Date of release	Description of changes
V01_00	2025-04-29	——

Attention

RoHS

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